

Jean-Pierre Raskin

List of Publications by Year in descending order

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364
papers

8,056
citations

53660

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h-index

88477

70
g-index

366
all docs

366
docs citations

366
times ranked

5817
citing authors

#	ARTICLE	IF	CITATIONS
1	Characterization of thin Al ₂ O ₃ /SiO ₂ dielectric stack for CMOS transistors. <i>Microelectronic Engineering</i> , 2022, 254, 111708.	1.1	10
2	Estimation of the Young's Modulus of Nanometer-Thick Films Using Residual Stress-Driven Bilayer Cantilevers. <i>Nanomaterials</i> , 2022, 12, 265.	1.9	1
3	Back-gate bias effect on the linearity of pocket doped FDSOI MOSFET. <i>Microelectronics Journal</i> , 2022, 121, 105365.	1.1	7
4	22 nm FD-SOI MOSFET Figures of Merit at high temperatures upto 175 °C. , 2022, , .		2
5	Back-Gate Lumped Resistance Effect on AC Characteristics of FD-SOI MOSFET. <i>IEEE Microwave and Wireless Components Letters</i> , 2022, 32, 704-707.	2.0	1
6	N _{ox} and Buried PN junctions effect on RF performance of High-Resistivity Silicon substrates. , 2022, , .		2
7	Low-power silicon strain sensor based on CMOS current reference topology. <i>Sensors and Actuators A: Physical</i> , 2022, 339, 113491.	2.0	0
8	Time Dependence of RF Losses in GaN-on-Si Substrates. <i>IEEE Microwave and Wireless Components Letters</i> , 2022, 32, 688-691.	2.0	2
9	Fully Depleted SOI Technology for Millimeter-Wave Integrated Circuits. <i>IEEE Journal of the Electron Devices Society</i> , 2022, 10, 424-434.	1.2	4
10	High-Resistivity Substrates with PN Interface Passivation in 22 nm FD-SOI. , 2022, , .		5
11	Impact of Substrate Resistivity on Spiral Inductors at MM-Wave Frequencies. <i>Solid-State Electronics</i> , 2022, , 108377.	0.8	3
12	Investigation and optimization of traps properties in Al ₂ O ₃ /SiO ₂ dielectric stacks using conductance method. <i>Solid-State Electronics</i> , 2022, 194, 108347.	0.8	2
13	Experimental study of thermal coupling effects in FD-SOI MOSFET. <i>Solid-State Electronics</i> , 2022, 194, 108362.	0.8	1
14	Development Of High Resistivity FD-SOI Substrates for mmWave Applications. <i>ECS Transactions</i> , 2022, 108, 31-45.	0.3	1
15	Porous silicon membranes and their applications: Recent advances. <i>Sensors and Actuators A: Physical</i> , 2021, 318, 112486.	2.0	29
16	Extensive Electrical Characterization Methodology of Advanced MOSFETs Towards Analog and RF Applications. <i>IEEE Journal of the Electron Devices Society</i> , 2021, 9, 500-510.	1.2	9
17	A Physical Model of Contact Resistance in Ti-Contacted Graphene-Based Field Effect Transistors. <i>IEEE Transactions on Electron Devices</i> , 2021, 68, 892-898.	1.6	4
18	Electrical Characterization of Cellulose-Based Membranes towards Pathogen Detection in Water. <i>Biosensors</i> , 2021, 11, 57.	2.3	6

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19	A Review on Functionalized Graphene Sensors for Detection of Ammonia. <i>Sensors</i> , 2021, 21, 1443.	2.1	61
20	Assessment of RF compact modelling of FD SOI transistors. , 2021, , .		1
21	SOI technologies for RF and millimeter-wave integrated circuits. , 2021, , .		2
22	On-chip environmentally assisted cracking in thin freestanding SiO ₂ films. <i>Journal of Materials Research</i> , 2021, 36, 2479-2494.	1.2	3
23	Back-Gate Network Extraction Free from Dynamic Self-Heating in FD SOI. , 2021, , .		0
24	On the Separate Extraction of Self-Heating and Substrate Effects in FD-SOI MOSFET. <i>IEEE Electron Device Letters</i> , 2021, 42, 665-668.	2.2	10
25	Improved Split CV Mobility Extraction in 28 nm Fully Depleted Silicon on Insulator Transistors. <i>IEEE Electron Device Letters</i> , 2021, 42, 661-664.	2.2	2
26	Characterization and role of deep traps on the radio frequency performances of high resistivity substrates. <i>Journal of Applied Physics</i> , 2021, 129, 215701.	1.1	0
27	Novel class of nanostructured metallic glass films with superior and tunable mechanical properties. <i>Acta Materialia</i> , 2021, 213, 116955.	3.8	32
28	Indirect light absorption model for highly strained silicon infrared sensors. <i>Journal of Applied Physics</i> , 2021, 130, .	1.1	6
29	In-situ TEM irradiation creep experiment revealing radiation induced dislocation glide in pure copper. <i>Acta Materialia</i> , 2021, 216, 117096.	3.8	6
30	Modeling of Semiconductor Substrates for RF Applications: Part II – Parameter Impact on Harmonic Distortion. <i>IEEE Transactions on Electron Devices</i> , 2021, 68, 4606-4613.	1.6	11
31	Modeling of Semiconductor Substrates for RF Applications: Part I – Static and Dynamic Physics of Carriers and Traps. <i>IEEE Transactions on Electron Devices</i> , 2021, 68, 4598-4605.	1.6	16
32	Heat sink implementation in back-end of line for self-heating reduction in 22-nm FDSOI MOSFETs. <i>Solid-State Electronics</i> , 2021, 184, 108088.	0.8	4
33	Rheology of amorphous olivine thin films characterized by nanoindentation. <i>Acta Materialia</i> , 2021, 219, 117257.	3.8	9
34	High performance silicon-based substrate using buried PN junctions towards RF applications. , 2021, , .		6
35	Field-Effect Passivation of Lossy Interfaces in High-Resistivity RF Silicon Substrates. , 2021, , .		1
36	CMOS compatible GaN-on-Si HEMT technology for RF applications: analysis of substrate losses and non-linearities. , 2021, , .		3

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37	Impact of III-N buffer layers on RF losses and harmonic distortion of GaN-on-Si Substrates. , 2021, , .		2
38	High-Temperature Characterization of Novel Silicon-Based Substrate Solutions for RF-IC Applications. , 2021, , .		1
39	Opto-electrical properties and internal stress in Al:ZnO thin films deposited by direct current reactive sputtering. Thin Solid Films, 2020, 695, 137760.	0.8	13
40	An ammonia sensor composed of polypyrrole synthesized on reduced graphene oxide by electropolymerization. Sensors and Actuators B: Chemical, 2020, 305, 127423.	4.0	64
41	Behavior of gold-doped silicon substrate under small- and large-RF signal. Solid-State Electronics, 2020, 168, 107718.	0.8	5
42	Post-process porous silicon for 5G applications. Solid-State Electronics, 2020, 168, 107719.	0.8	14
43	Structural and nanomechanical properties of porous silicon: Cheap substrate for CMOS process industry. Surface and Interface Analysis, 2020, 52, 1055-1060.	0.8	1
44	DC-40 GHz SPDTs in 22 nm FD-SOI and Back-Gate Impact Study. , 2020, , .		12
45	Material and manufacturing process selection for electronics eco-design: Case study on paper-based water quality sensors. Procedia CIRP, 2020, 90, 344-349.	1.0	8
46	A novel displacement cascade driven irradiation creep mechanism in $\hat{\pm}$ -zirconium: A molecular dynamics study. Journal of Nuclear Materials, 2020, 541, 152336.	1.3	11
47	Broadband Smart mmWave Front-End-Modules in Advanced FD-SOI with Adaptive-Biasing and Tuning of Distributed Antenna-Arrays. , 2020, , .		3
48	Effective resistivity extraction of low-loss silicon substrates at millimeter-wave frequencies. International Journal of Microwave and Wireless Technologies, 2020, 12, 615-628.	1.5	9
49	SOI Devices and Substrates towards RF and Millimeter Wave ICs. , 2020, , .		2
50	Fundamental limitations in transferred CVD graphene caused by Cu catalyst surface morphology. Carbon, 2020, 163, 95-104.	5.4	40
51	28-nm FD-SOI CMOS RF Figures of Merit Down to 4.2 K. IEEE Journal of the Electron Devices Society, 2020, 8, 646-654.	1.2	27
52	Self-Heating in FDSOI UTBB MOSFETs at Cryogenic Temperatures and its Effect on Analog Figures of Merit. IEEE Journal of the Electron Devices Society, 2020, 8, 789-796.	1.2	11
53	TEM investigation of the role of the polycrystalline-silicon film/substrate interface in high quality radio frequency silicon substrates. Materials Characterization, 2020, 161, 110174.	1.9	3
54	Impact of gate to source/drain alignment on the static and RF performance of junctionless Si nanowire n-MOSFETs. Solid-State Electronics, 2020, 169, 107817.	0.8	0

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55	Electrical characterization of advanced MOSFETs towards analog and RF applications. , 2020, , .		1
56	Effect of Heat Sink in Back-End of Line on Self-Heating in 22 nm FDSOI MOSFETs. , 2020, , .		3
57	Substrate RF Losses and Non-linearities in GaN-on-Si HEMT Technology. , 2020, , .		9
58	Electrochemical Characterization of Nitrocellulose Membranes towards Bacterial Detection in Water. , 2020, 60, .		0
59	Multi-wafer batch synthesis of graphene on Cu films by quasi-static flow chemical vapor deposition. 2D Materials, 2019, 6, 045032.	2.0	16
60	Post-process local porous silicon integration method for RF application. , 2019, , .		3
61	Silicon-substrate enhancement technique enabling high quality integrated RF passives. , 2019, , .		12
62	Atomic-scale viscoplasticity mechanisms revealed in high ductility metallic glass films. Scientific Reports, 2019, 9, 13426.	1.6	13
63	<i>(Invited)</i> SOI Technologies for RF and Millimeter Wave Applications. ECS Transactions, 2019, 92, 79-94.	0.3	20
64	Chemical Sensors for VOC Detection in Indoor Air: Focus on Formaldehyde. NATO Science for Peace and Security Series A: Chemistry and Biology, 2019, , 47-70.	0.5	0
65	Detection mechanism in highly sensitive ZnO nanowires network gas sensors. Sensors and Actuators B: Chemical, 2019, 297, 126602.	4.0	28
66	Probing carrier concentration in gated single, bi- and tri-layer CVD graphene using Raman spectroscopy. Carbon, 2019, 149, 390-399.	5.4	24
67	28-nm FDSOI nMOSFET RF Figures of Merits and Parasitic Elements Extraction at Cryogenic Temperature Down to 77 K. IEEE Journal of the Electron Devices Society, 2019, 7, 810-816.	1.2	12
68	28-nm FDSOI analog and RF Figures of Merit at N2 cryogenic temperatures. Solid-State Electronics, 2019, 159, 77-82.	0.8	21
69	Enhanced ultraviolet photoresponse in a graphene-gated ultra-thin Si-based photodiode. Journal Physics D: Applied Physics, 2019, 52, 245101.	1.3	10
70	Chemically deposited palladium nanoparticles on graphene for hydrogen sensor applications. Scientific Reports, 2019, 9, 3653.	1.6	57
71	Ultra Low-Loss Si Substrate for On-Chip UWB GHz Antennas. IEEE Journal of the Electron Devices Society, 2019, 7, 393-397.	1.2	7
72	Low-Loss Si-Substrates Enhanced Using Buried PN Junctions for RF Applications. IEEE Electron Device Letters, 2019, 40, 690-693.	2.2	23

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73	Effective Resistivity Extraction of Low-Loss Silicon Substrate at Millimeter-Wave Frequencies. , 2019, , .		4
74	Self-Heating in 28 FDSOI UTBB MOSFETs at Cryogenic Temperatures. , 2019, , .		4
75	Crack on a chip test method for thin freestanding films. Journal of the Mechanics and Physics of Solids, 2019, 123, 267-291.	2.3	8
76	28 FDSOI RF Figures of Merit down to 4.2 K. , 2019, , .		5
77	A SPDT RF Switch Small- and Large-Signal Characteristics on TR-HR SOI Substrates. IEEE Journal of the Electron Devices Society, 2018, 6, 543-550.	1.2	19
78	Small- and Large-Signal Performance Up To 175 Å°C of Low-Cost Porous Silicon Substrate for RF Applications. IEEE Transactions on Electron Devices, 2018, 65, 1887-1895.	1.6	19
79	Hemispherical cavities on silicon substrates: an overview of micro fabrication techniques. Materials Research Express, 2018, 5, 045702.	0.8	2
80	Role of Cu foil in-situ annealing in controlling the size and thickness of CVD graphene domains. Carbon, 2018, 129, 270-280.	5.4	61
81	Intrinsic rectification in common-gated graphene field-effect transistors. Nano Energy, 2018, 43, 37-46.	8.2	10
82	Extrinsic gate capacitance compact model for UTBB MOSFETs. Semiconductor Science and Technology, 2018, 33, 015001.	1.0	1
83	Fully Depleted SOI technologies from digital to RF and beyond. , 2018, , .		1
84	Role of the Cu substrate in the growth of ultra-flat crack-free highly-crystalline single-layer graphene. Nanoscale, 2018, 10, 21898-21909.	2.8	24
85	Design and Modeling of a MEMS Dual-Backplate Capacitive Microphone with Spring-Supported Diaphragm for Mobile Device Applications. Sensors, 2018, 18, 3545.	2.1	16
86	A Fast and Room-Temperature Operation Ammonia Sensor Based on Compound of Graphene With Polypyrrole. IEEE Sensors Journal, 2018, 18, 9088-9096.	2.4	39
87	Raman analysis of strain in p-type doped silicon nanostructures. Journal of Applied Physics, 2018, 124, .	1.1	4
88	Ellipsometry-based conductivity extraction in case of phosphorus doped polysilicon. Journal of Materials Science: Materials in Electronics, 2018, 29, 11627-11636.	1.1	2
89	Linear and non-linear electrical behaviors in graphene ribbon based devices. Journal of Science: Advanced Materials and Devices, 2018, 3, 366-370.	1.5	4
90	RF Small- and Large-Signal Characteristics of CPW and TFMS Lines on Trap-Rich HR-SOI Substrates. IEEE Transactions on Electron Devices, 2018, 65, 3120-3126.	1.6	4

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91	Optical Fibre NO ₂ Sensor Based on Lutetium Bisphthalocyanine in a Mesoporous Silica Matrix. Sensors, 2018, 18, 740.	2.1	8
92	(Invited) Current Status and Trends in RF Silicon-on-Insulator Material and Device. ECS Transactions, 2018, 85, 47-57.	0.3	0
93	Prediction of <scp>RF</scp> performances of advanced <scp>MOS</scp> transistors from <scp>DC</scp> and low frequency measurements. Microwave and Optical Technology Letters, 2018, 60, 2256-2262.	0.9	2
94	Design of a Novel MEMS Microgripper with Rotatory Electrostatic Comb-Drive Actuators for Biomedical Applications. Sensors, 2018, 18, 1664.	2.1	35
95	Raman and XPS characterization of vanadium oxide thin films with temperature. Applied Surface Science, 2017, 403, 717-727.	3.1	216
96	Pressure-Controlled Chemical Vapor Deposition of Single-Layer Graphene with Millimeter-Size Domains on Thin Copper Film. Chemistry of Materials, 2017, 29, 3431-3440.	3.2	34
97	Absorption modulation of FSS-polymer nanocomposites through incorporation of conductive nanofillers. Applied Physics A: Materials Science and Processing, 2017, 123, 1.	1.1	8
98	Creep behavior of submicron copper films under irradiation. Acta Materialia, 2017, 131, 77-87.	3.8	11
99	Adhesionless and near-ideal contact behavior of graphene on Cu thin film. Carbon, 2017, 122, 446-450.	5.4	17
100	A Quasi-Static Model of Silicon Substrate Effects in Graphene Field Effect Transistors. IEEE Electron Device Letters, 2017, 38, 987-990.	2.2	5
101	Homogeneous flow and size dependent mechanical behavior in highly ductile Zr ₆₅ Ni ₃₅ metallic glass films. Acta Materialia, 2017, 131, 246-259.	3.8	72
102	Mechanical behavior of ultrathin sputter deposited porous amorphous Al ₂ O ₃ films. Acta Materialia, 2017, 125, 27-37.	3.8	20
103	Defect-free functionalized graphene sensor for formaldehyde detection. Nanotechnology, 2017, 28, 055501.	1.3	22
104	Internal stress and opto-electronic properties of ZnO thin films deposited by reactive sputtering in various oxygen partial pressures. Journal of Applied Physics, 2017, 122, .	1.1	9
105	Review on analog/radio frequency performance of advanced silicon MOSFETs. Semiconductor Science and Technology, 2017, 32, 123004.	1.0	31
106	Comparative study of non-linearities in 28 nm node FDSOI and Bulk MOSFETs. , 2017, , .		9
107	Analog and RF analysis of gate all around silicon nanowire MOSFETs. , 2017, , .		5
108	Automated layout-integrated sizing of a 2.45 GHz differential-drive rectifier in 28 nm FDSOI CMOS. , 2017, , .		0

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109	Compact On-Wafer Test Structures for Device RF Characterization. IEEE Transactions on Electron Devices, 2017, 64, 3101-3107.	1.6	2
110	High quality silicon-based substrates for microwave and millimeter wave passive circuits. Solid-State Electronics, 2017, 135, 78-84.	0.8	11
111	RF SOI CMOS technology on 1st and 2nd generation trap-rich high resistivity SOI wafers. Solid-State Electronics, 2017, 128, 121-128.	0.8	13
112	RF harmonic distortion modeling in silicon-based substrates including non-equilibrium carrier dynamics. , 2017, , .		4
113	Back-gate bias effect on UTBB-FDSOI non-linearity performance. , 2017, , .		5
114	A Formaldehyde Sensor Based on Molecularly-Imprinted Polymer on a TiO ₂ Nanotube Array. Sensors, 2017, 17, 675.	2.1	55
115	SOI Technologies from Microelectronics to Microsystems â€” Meeting the <i>More than Moore</i> Roadmap Requirements. , 2017, , .		0
116	Surveying colloid sedimentation by coplanar waveguides. Nanotechnology, 2016, 27, 225502.	1.3	1
117	Compact ultra-wideband bandpass filter with notch band based on the impedance matching method. Microwave and Optical Technology Letters, 2016, 58, 2176-2178.	0.9	1
118	Efficient passive energy harvesters at 950 MHz and 2.45 GHz for 100 $\frac{1}{4}$ W applications in 65 nm CMOS. , 2016, , .		1
119	Semiconductor- to metallic-like behavior in Bi thin films on KCl substrate. Journal of Applied Physics, 2016, 119, 135304.	1.1	1
120	A generic â€œmicro-Stoneyâ€ method for the measurement of internal stress and elastic modulus of ultrathin films. Review of Scientific Instruments, 2016, 87, 015002.	0.6	9
121	Acetaldehyde Chemical Sensor based on Molecularly Imprinted Polypyrrole. Procedia Engineering, 2016, 168, 569-573.	1.2	8
122	A novel on chip test method to characterize the creep behavior of metallic layers under heavy ion irradiation. Journal of Nuclear Materials, 2016, 476, 20-29.	1.3	13
123	SOI technology pushes the limits of CMOS for RF applications. , 2016, , .		14
124	Automated Design of a 13.56 MHz 19 μ W Passive Rectifier With 72% Efficiency Under 10 μ A load. IEEE Journal of Solid-State Circuits, 2016, 51, 1290-1301.	3.5	22
125	The role of SiC as a diffusion barrier in the formation of graphene on Si(111). Diamond and Related Materials, 2016, 66, 141-148.	1.8	5
126	FinFET and UTBB for RF SOI communication systems. Solid-State Electronics, 2016, 125, 73-81.	0.8	18

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127	Automated design of a 13.56 MHz corner-robust efficient differential drive rectifier for 10 $\hat{I}_{1/4}$ A load. , 2016, , .		3
128	Size dependent fracture strength and cracking mechanisms in freestanding polycrystalline silicon films with nanoscale thickness. Engineering Fracture Mechanics, 2016, 168, 190-203.	2.0	13
129	Parasitic Gate Resistance Impact on Triple-Gate FinFET CMOS Inverter. IEEE Transactions on Electron Devices, 2016, 63, 2635-2642.	1.6	9
130	Assessment of 28 nm UTBB FD-SOI technology platform for RF applications: Figures of merit and effect of parasitic elements. Solid-State Electronics, 2016, 117, 130-137.	0.8	45
131	A versatile lab-on-chip test platform to characterize elementary deformation mechanisms and electromechanical couplings in nanoscopic objects. Comptes Rendus Physique, 2016, 17, 485-495.	0.3	13
132	Comparison of self-heating and its effect on analogue performance in 28 nm bulk and FDSOI. Solid-State Electronics, 2016, 115, 219-224.	0.8	21
133	Damage evaluation in graphene underlying atomic layer deposition dielectrics. Scientific Reports, 2015, 5, 13523.	1.6	32
134	Dislocation-mediated relaxation in nanograined columnar palladium films revealed by on-chip time-resolved HRTEM testing. Nature Communications, 2015, 6, 5922.	5.8	53
135	Trigate nanowire MOSFETs analog figures of merit. Solid-State Electronics, 2015, 112, 78-84.	0.8	15
136	On-chip fracture testing of freestanding nanoscale materials. Engineering Fracture Mechanics, 2015, 150, 222-238.	2.0	19
137	Extraction Method for the Residual Stress in Multilayer Microplates Under Large Deflection Based on Static Deflection Analysis. Journal of Microelectromechanical Systems, 2015, 24, 1150-1163.	1.7	2
138	RF modeling of 40nm SOI triple-gate FinFET. International Journal of Numerical Modelling: Electronic Networks, Devices and Fields, 2015, 28, 465-478.	1.2	10
139	Mechanical characterization and modelling of Lorentz force based MEMS magnetic field sensors. Solid-State Electronics, 2015, 112, 68-77.	0.8	13
140	High resistivity SOI wafer for mainstream RF System-on-Chip. , 2015, , .		7
141	A MEMS-based magnetic field sensor with simple resonant structure and linear electrical response. Microelectronic Engineering, 2015, 142, 12-21.	1.1	23
142	Wide frequency band assessment of 28nm FDSOI technology platform for analogue and RF applications. Solid-State Electronics, 2015, 108, 47-52.	0.8	29
143	Extrinsic mechanical size effects in thin ZrNi metallic glass films. Acta Materialia, 2015, 90, 232-241.	3.8	89
144	FinFET versus UTBB SOI — A RF perspective. , 2015, , .		10

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145	Multiscale modelling framework for the fracture of thin brittle polycrystalline films: application to polysilicon. Computational Mechanics, 2015, 55, 73-91.	2.2	14
146	Assessment of Global Variability in UTBB MOSFETs in Subthreshold Regime. Journal of Low Power Electronics and Applications, 2014, 4, 201-213.	1.3	8
147	RF and non-linearity characterization of porous silicon layer for RF-ICs. , 2014, , .		2
148	High resistivity SOI wafer for mainstream RF System-on-Chip. , 2014, , .		1
149	Low-cost wideband double-layer microstrip coupled-line directional coupler with high directivity. Microwave and Optical Technology Letters, 2014, 56, 1570-1575.	0.9	0
150	Impact of field-induced quantum confinement on the onset of tunneling field-effect transistors: Experimental verification. Applied Physics Letters, 2014, 105, .	1.5	9
151	28 nm FD SOI Technology Platform RF FoM. , 2014, , .		5
152	Plasticity mechanisms in ultrafine grained freestanding aluminum thin films revealed by <i>in-situ</i> transmission electron microscopy nanomechanical testing. Applied Physics Letters, 2014, 104, .	1.5	32
153	Analysis of slow-wave propagation in coplanar transmission lines with inkjet printed multiwalled carbon nanotubes network. Microwave and Optical Technology Letters, 2014, 56, 1118-1124.	0.9	1
154	Roughness analysis in strained silicon-on-insulator wires and films. Journal of Applied Physics, 2014, 116, 124503.	1.1	2
155	Variability of UTBB MOSFET analog figures of merit in wide frequency range. , 2014, , .		3
156	Compositional-induced structural change in Zr_xNi_{100-x} thin film metallic glasses. Journal of Alloys and Compounds, 2014, 615, S348-S351.	2.8	36
157	On the gm/ID-based approaches for threshold voltage extraction in advanced MOSFETs and their application to ultra-thin body SOI MOSFETs. Solid-State Electronics, 2014, 97, 52-58.	0.8	17
158	Exploring the mechanical size effects in Zr65Ni35 thin film metallic glasses. Journal of Alloys and Compounds, 2014, 615, S90-S92.	2.8	25
159	Out-of-plane MEMS-based mechanical airflow sensor co-integrated in SOI CMOS technology. Sensors and Actuators A: Physical, 2014, 206, 67-74.	2.0	21
160	Silicon-on-insulator MOSFETs models in analog/RF domain. International Journal of Numerical Modelling: Electronic Networks, Devices and Fields, 2014, 27, 707-735.	1.2	17
161	Wide frequency band assessment of 28 nm FDSOI technology platform for analogue and RF applications. , 2014, , .		16
162	Self-formation of sub-10 nm nanogaps based on silicidation. Nanotechnology, 2014, 25, 115201.	1.3	1

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163	Size-dependent failure mechanisms in ZrNi thin metallic glass films. Scripta Materialia, 2014, 89, 9-12.	2.6	34
164	RF Performance of SOI CMOS Technology on Commercial 200-mm Enhanced Signal Integrity High Resistivity SOI Substrate. IEEE Transactions on Electron Devices, 2014, 61, 722-728.	1.6	49
165	Direct growth of graphene on Si(111). Journal of Applied Physics, 2014, 115, 223704.	1.1	21
166	Fracture toughness measurement of ultra-thin hard films deposited on a polymer interlayer. Thin Solid Films, 2014, 550, 464-471.	0.8	10
167	Effect of parasitic elements on UTBB FD SOI MOSFETs RF figures of merit. Solid-State Electronics, 2014, 97, 38-44.	0.8	36
168	Effect of temperature on advanced Si-based substrates performance for RF passive integration. Microelectronic Engineering, 2014, 120, 205-209.	1.1	13
169	Partially Depleted SOI Versus Deep N-Well Protected Bulk-Si MOSFETs: A High-Temperature RF Study for Low-Voltage Low-Power Applications. IEEE Transactions on Microwave Theory and Techniques, 2013, 61, 1496-1504.	2.9	10
170	Direct growth of graphitic carbon on Si(111). Applied Physics Letters, 2013, 102, .	1.5	24
171	Fringing gate capacitance model for triple-gate FinFET. , 2013, , .		6
172	Photo-Induced Coplanar Waveguide RF Switch and Optical Crosstalk on High-Resistivity Silicon Trap-Rich Passivated Substrate. IEEE Transactions on Electron Devices, 2013, 60, 3478-3484.	1.6	6
173	RF MEMS Passives on High-Resistivity Silicon Substrates. IEEE Microwave and Wireless Components Letters, 2013, 23, 632-634.	2.0	36
174	The fracture studies of polycrystalline silicon based MEMS. , 2013, , .		2
175	Impact of Extrinsic Capacitances on FinFET RF Performance. IEEE Transactions on Microwave Theory and Techniques, 2013, 61, 833-840.	2.9	100
176	UTBB SOI MOSFETs analog figures of merit: Effects of ground plane and asymmetric double-gate regime. Solid-State Electronics, 2013, 90, 56-64.	0.8	44
177	Is high resistivity SOI wafer the substrate solution for RF System-on-Chip?. , 2013, , .		0
178	CVD synthesis of mono- and few-layer graphene using alcohols at low hydrogen concentration and atmospheric pressure. Chemical Physics Letters, 2013, 584, 142-146.	1.2	43
179	A comprehensive review on microwave FinFET modeling for progressing beyond the state of art. Solid-State Electronics, 2013, 80, 81-95.	0.8	121
180	RF and linear performance of commercial 200 mm trap-rich HR-SOI wafers for SoC applications. , 2013, , .		15

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181	Twisted Bilayer Graphene: Microscopic Rainbows. <i>Small</i> , 2013, 9, 3247-3251.	5.2	30
182	Surface states and conductivity of silicon nano-wires. <i>Journal of Applied Physics</i> , 2013, 113, 134502.	1.1	13
183	Raman scattering study of the phonon dispersion in twisted bilayer graphene. <i>Nano Research</i> , 2013, 6, 269-274.	5.8	85
184	Advanced Si-based substrates for RF passive integration: Comparison between local porous Si layer technology and trap-rich high resistivity Si. <i>Solid-State Electronics</i> , 2013, 87, 27-33.	0.8	27
185	Inter- and intragranular plasticity mechanisms in ultrafine-grained Al thin films: An in situ TEM study. <i>Acta Materialia</i> , 2013, 61, 205-216.	3.8	106
186	Design guidelines for releasing silicon nanowire arrays by liquid and vapor phase hydrofluoric acid. <i>Microelectronic Engineering</i> , 2013, 103, 57-65.	1.1	6
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